

General Description

The 2SB1204 is PNP silicon power transistor, Designed for general purpose amplifier and low speed switching applications.

Features

- Epitaxial Planar Die Construction
- Low Collector-Emitter Saturation Voltage
- RoHS Compliant

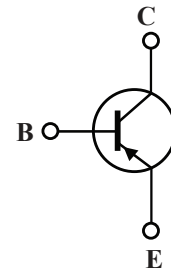
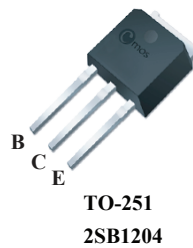
Product Summary

VCBO	VCEO	IC
-70V	-50V	-6A

Applications

- Ideal for Medium Power Switching

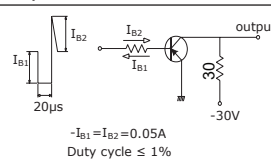
TO-251 Pin Configuration



Absolute Maximum Ratings(Ta = 25°C)

Symbol	Parameter	Rating	Units
V _{CB0}	Collector to Base Voltage	-70	V
V _{CE0}	Collector to Emitter Voltage	-50	V
V _{EB0}	Emitter-Base Voltage	-6	V
I _C	Collector Current	-6	A
I _{CP}	Collector Current (Pulse)	-8	A
P _C	Collector Dissipation(T _c =25°C)	20	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Junction Temperature	150	°C

Electrical Characteristics (Ta =25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit	
Collector Cutoff Current	ICBO	V _{CB} =-80V, I _E =0A			-500	nA	
Emitter Cutoff Current	IEBO	V _{EB} =-5V, I _C =0A			-500	nA	
DC Current Gain	hFE	V _{CE} =-2V, I _C =-5mA	100*		500*		
Gain-Bandwidth Product	f T	V _{CE} =-5V, I _C =-100mA		110		MHz	
Output Capacitance	Cob	V _{CB} =-10V, f=1MHz		25		pF	
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =-2A, I _B =-200mA		-0.23	-0.6	V	
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =-1A, I _B =-100mA		-0.91	-1.5	V	
Collector-to-Base Breakdown Voltage	V _{(BR)CBO}	I _C =-2mA, I _E =0A	-70			V	
Collector-to-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =-2mA, R _{BE} =∞	-50			V	
Emitter-to-Base Breakdown Voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0A	-6			V	
Turn-ON Time	t _{on}	 <p style="text-align: center;">-I_{B1} = I_{B2} = 0.05A Duty cycle ≤ 1%</p>		100		ns	
Storage Time	t _{stg}				300		ns
Fall Time	t _f				50		ns

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